

HERMETICALLY SEALED GLASS PACKAGED TUNING DIODES

ABRUPT and HYPERABRUPT

ELECTRICAL CHARACTERISTICS (T_A = 25° C unless otherwise noted)

Diode Cap. (CT) [*] ±10% @ 4V/1 MHz pF	GENERAL APPLICATIONS			LOW INDUCTANCE FOR USE TO 2.5 GHz			MINIATURE GLASS VERY HIGH Q			VERY HIGH Q PREDICTABLE TRACKING			GENERAL PURPOSE			
	TYPE NO.	RATIO C ₂ /C ₂₀ min/typ	Q ₄ @ 50 MHz	TYPE NO.	RATIO C ₂ /C ₂₀ min/max	Q ₄ @ 50 MHz min	TYPE NO.	RATIO C ₂ /C ₃₀ min/typ	Q ₄ @ 50 MHz min	TYPE NO.	RATIO C ₂ /C ₃₀ min/typ	Q ₄ @ 50 MHz min	TYPE NO.	RATIO C ₄ /C ₂₅ min/typ	Q ₄ @ 50 MHz	pF
1.8																1.8
2.2																2.2
2.7																2.7
3.3																3.3
3.9																3.9
4.7																4.7
5.6																5.6
6.8																6.8
8.2																8.2
10.0																10.0
12.0																12.0
15.0																15.0
18.0																18.0
20.0																20.0
22.0																22.0
27.0																27.0
33.0																33.0
39.0																39.0
47.0																47.0
56.0																56.0
68.0																68.0
82.0																82.0
100.0																100.0
VR (min)	20 Vdc @ IR = 10 uAdc			25 Vdc @ IR = 10 uAdc			30 Vdc @ IR = 10 uAdc			30 Vdc @ IR = 10 uAdc			30 Vdc @ IR = 10 uAdc			
IR (max)	0.1 uAdc @ VR = 15 Vdc			0.5 uAdc @ VR = 20 Vdc			0.02 uAdc @ VR = 25 Vdc 2.0 uAdc @ TA = 150°C			0.02 uAdc @ VR = 25 Vdc 2.0 uAdc @ TA = 150°C			0.2 uAdc @ VR = 25 Vdc			
TCC1	300 ppm/°C			300 ppm/°C			300 ppm/°C			300 ppm/°C			300 ppm/°C			
Case	DO 7			DO 35			Miniature DO 7			DO 7			DO 7			

15 & 20 VOLTS				
	TYPE NO.	RATIO C ₂ /C ₂₀ typ	Q ₄ @ 20 MHz min	
Diode Cap. (CT) [*] 4V/1 MHz ± 10% pF	120.0	MV1652	2.6	250
	150.0	MV1654	2.6	250
	180.0	MV1656	2.6	200
	200.0	MV1658	2.6	200
	220.0	MV1660	2.6	150
	250.0	MV1662	2.3	150
VR (min)	20 Vdc @ IR = 10 uAdc MV1652/60			
	15 Vdc @ IR = 10 uAdc MV1662/66			
IR (max)	0.1 uAdc @ VR = 15 Vdc MV1652/60			
	0.1 uAdc @ VR = 10 Vdc MV1662/66			
TCC	300 ppm/°C			
Case	DO-14			

^{*}Total Diode Capacitance measured at 1 MHz and VR specified. To order devices with CT Nom ± 5.0% or ± 2.0% add Suffix B or C respectively.

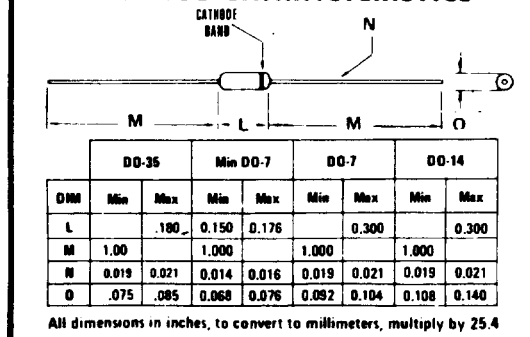
- (1) Capacitance Temperature Coefficient (typ) @ 4V/1 MHz
- (2) For SQ1716, C4 = 3 pf. nom.
- (3) Tuning Ratio @ C2/C15 for MV1662/66.

GENERAL SPECIFICATIONS

(25° C unless noted)

RATING	SYMBOL	VALUE
Reverse Voltage	VR	As SPECIFIED
Junction Temperature	T _j	+175°C Max
Storage Temperature	T _{stg}	-65°C to 200°C
Linear Power Derating		4 mW/°C
Device Dissipation (mW Max)	PD	400 250 400 500
Case Capacitance (pf Typ)	CC	0.10 0.15 0.2 0.3
Series Inductance (nhy Typ)	LS	1.5 3.0 5.0 5.0

PACKAGE CHARACTERISTICS



For other types not listed here, please contact your representative or the factory with your requirements.